


AO4707
P-Channel Enhancement Mode Field Effect Transistor with Schottky Diode
General Description

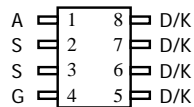
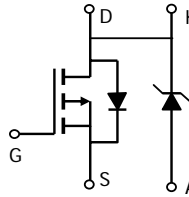
The AO4707 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. A Schottky diode is provided to facilitate the implementation of non-synchronous DC-DC converters. *Standard Product AO8820 is Pb-free (meets ROHS & Sony 259 specifications). AO8820L is a Green Product ordering option. AO8820 and AO8820L are electrically identical.*

Features

V_{DS} (V) = -30V
 I_D = -8A (V_{GS} = -10V)
 $R_{DS(ON)}$ < 33m Ω (V_{GS} = -10V)
 $R_{DS(ON)}$ < 56m Ω (V_{GS} = -4.5V)

SCHOTTKY

V_{DS} (V) = 30V, I_F = 3A, V_F < 0.52V@3A


SOIC-8

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	V_{DS}	-30		V
Gate-Source Voltage	V_{GS}	± 20		V
Continuous Drain Current ^A	I_D	$T_A=25^\circ\text{C}$	-8	A
		$T_A=70^\circ\text{C}$	-6.6	
Pulsed Drain Current ^B	I_{DM}	-40		
Schottky reverse voltage	V_{KA}		30	V
Continuous Forward Current ^A	I_F	$T_A=25^\circ\text{C}$	5	A
		$T_A=70^\circ\text{C}$	3.5	
Pulsed Forward Current ^B	I_{FM}		30	
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	3	W
		$T_A=70^\circ\text{C}$	2	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

Parameter: Thermal Characteristics MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10\text{s}$	$R_{\theta JA}$	24	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	Steady-State		54	75	
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	21	30	
Thermal Characteristics Schottky					
Maximum Junction-to-Ambient ^A	$t \leq 10\text{s}$	$R_{\theta JA}$	36	40	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	Steady-State		67	75	
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	25	30	

Electrical Characteristics ($T_J=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-24\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^\circ\text{C}$			-1 -5	μA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.2	-2	-2.4	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-10\text{V}$, $I_D=-8\text{A}$ $T_J=125^\circ\text{C}$		24.5 33	33	m Ω
		$V_{GS}=-4.5\text{V}$, $I_D=-5\text{A}$		41	56	m Ω
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-8\text{A}$		14.5		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		-0.76	-1	V
I_S	Maximum Body-Diode Continuous Current				-4.2	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-15\text{V}$, $f=1\text{MHz}$		920		pF
C_{oss}	Output Capacitance			190		pF
C_{rss}	Reverse Transfer Capacitance			122		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		3.6		Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $I_D=-8\text{A}$		18.4		nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			9.3		nC
Q_{gs}	Gate Source Charge			2.7		nC
Q_{gd}	Gate Drain Charge			4.9		nC
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=-10\text{V}$, $V_{DS}=-15\text{V}$, $R_L=1.8\Omega$, $R_{GEN}=3\Omega$		7.1		ns
t_r	Turn-On Rise Time			3.4		ns
$t_{D(off)}$	Turn-Off Delay Time			18.9		ns
t_f	Turn-Off Fall Time			8.4		ns
t_{rr}	Body Diode Reverse Recovery Time		$I_F=-8\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		21.5	
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-8\text{A}$, $di/dt=100\text{A}/\mu\text{s}$		12.5		nC
SCHOTTKY PARAMETERS						
V_F	Forward Voltage Drop	$I_F=3.0\text{A}$		0.48	0.52	V
I_{rm}	Maximum reverse leakage current	$V_R=24\text{V}$		0.07	0.15	mA
		$V_R=24\text{V}$, $T_J=125^\circ\text{C}$		4.2	20	
		$V_R=24\text{V}$, $T_J=150^\circ\text{C}$		15	60	
C_T	Junction Capacitance	$V_R=15\text{V}$		120		pF

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$.

The value in any given application depends on the user's specific board design. The current rating is based on the $t \leq 10\text{s}$ thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to lead $R_{\theta JL}$ and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ\text{C}$. The SOA curve provides a single pulse rating.

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P-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

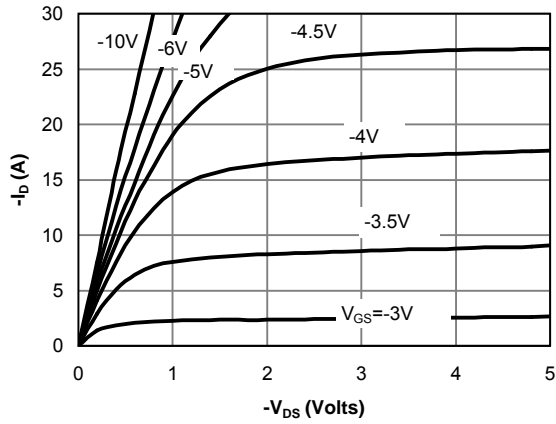


Fig 1: On-Region Characteristics

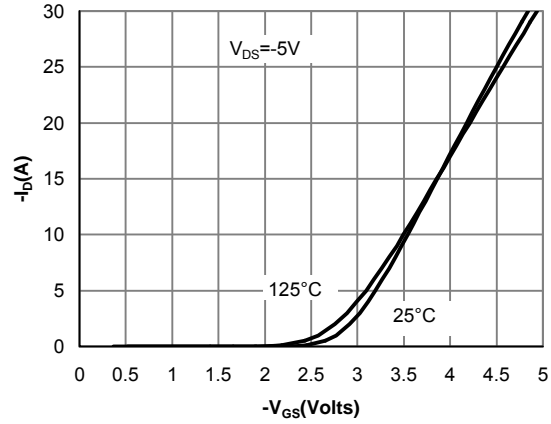


Figure 2: Transfer Characteristics

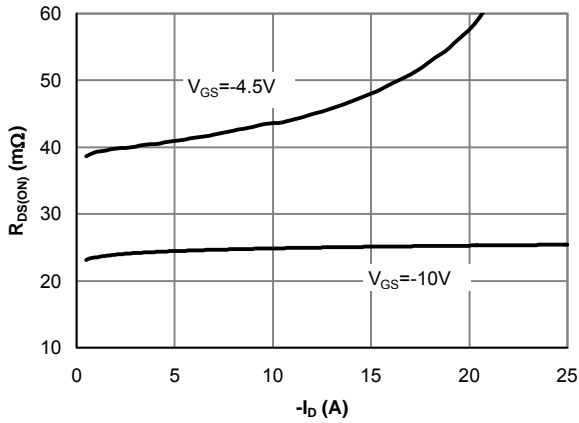


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

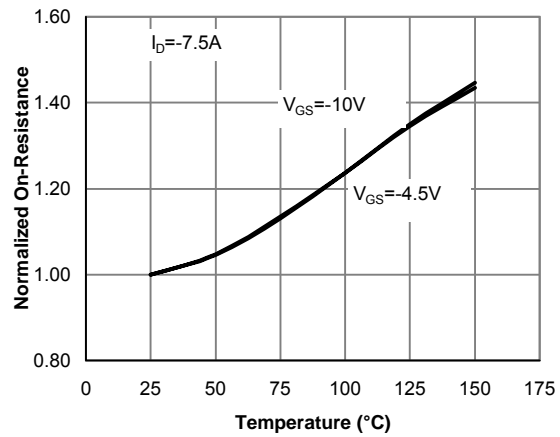


Figure 4: On-Resistance vs. Junction Temperature

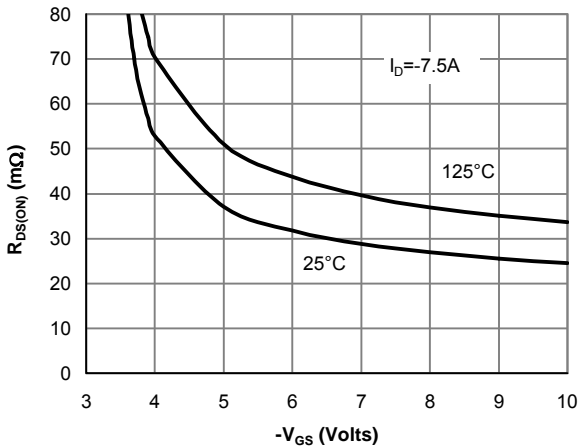


Figure 5: On-Resistance vs. Gate-Source Voltage

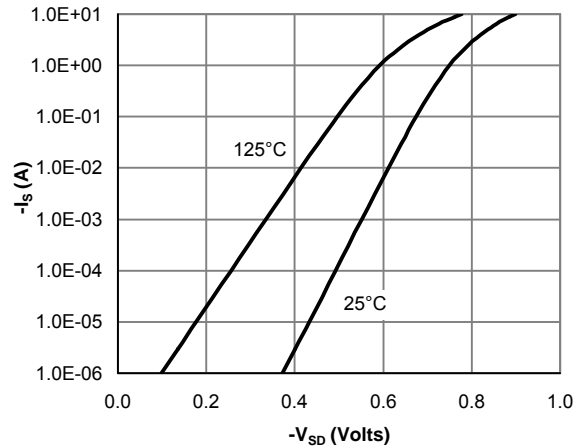


Figure 6: Body-Diode Characteristics

P-CHANNEL: TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

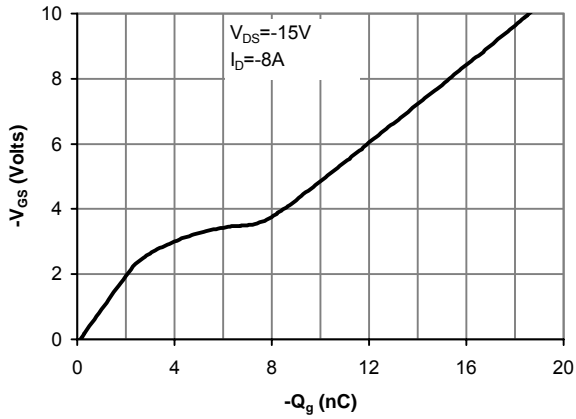


Figure 7: Gate-Charge Characteristics

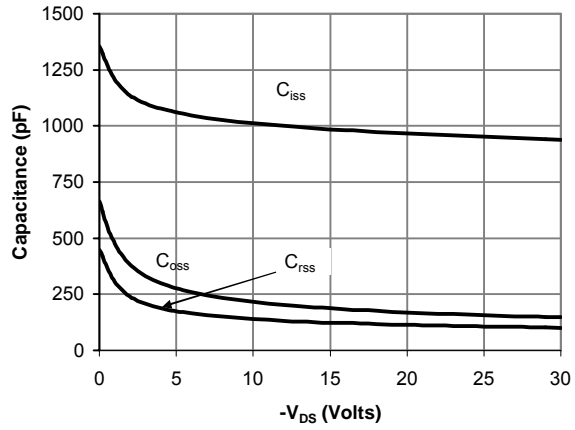


Figure 8: Capacitance Characteristics

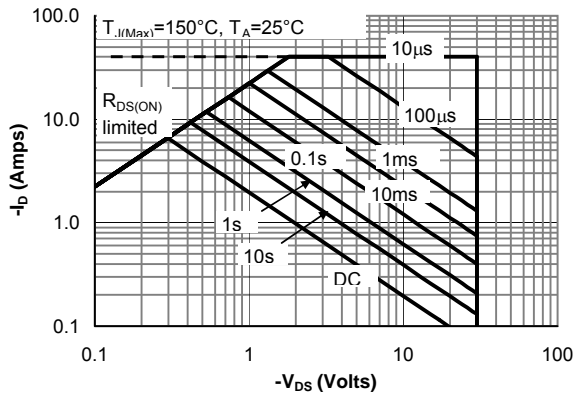


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

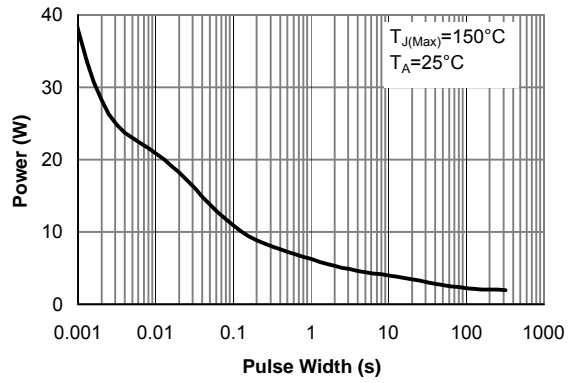


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

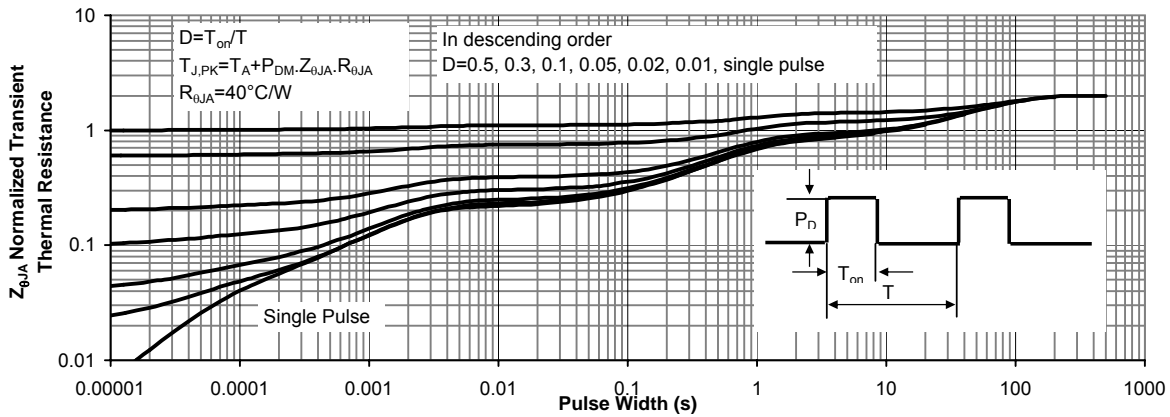


Figure 11: Normalized Maximum Transient Thermal Impedance

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: SCHOTTKY

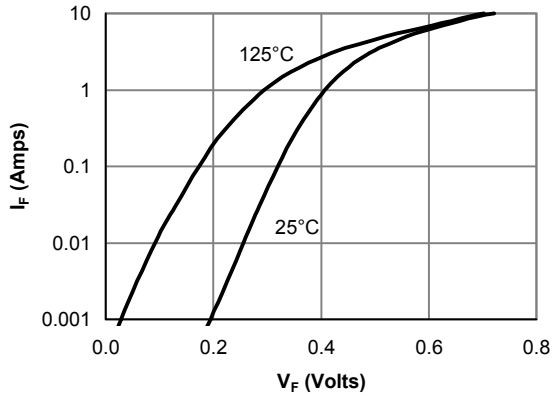


Figure 12: Schottky Forward Characteristics

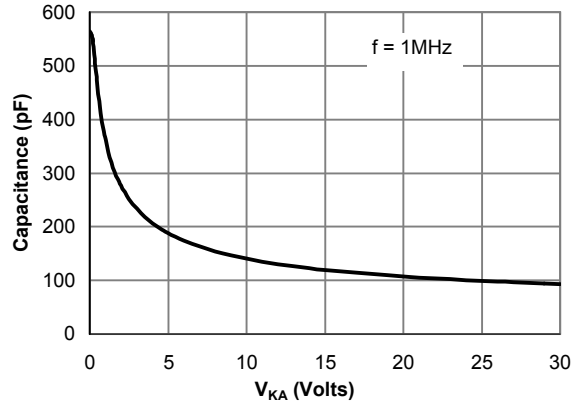


Figure 13: Schottky Capacitance Characteristics

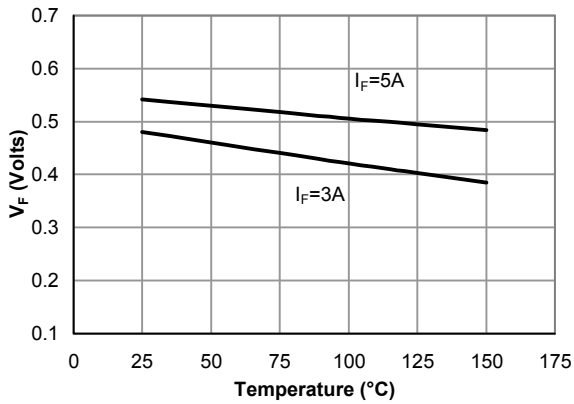


Figure 14: Schottky Forward Drop vs. Junction Temperature

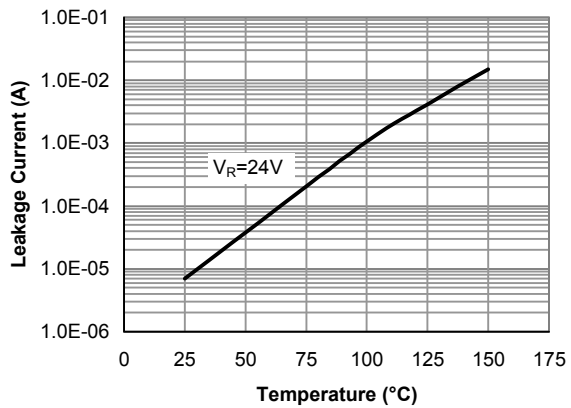


Figure 15: Schottky Leakage Current vs. Junction Temperature

